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Product data sheet

1. Product profile

1.1 General description

NPN medium power transistors in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package			Package		e number Package	kage		PNP complement
	NXP	JEITA	JEDEC						
BCP56H	SOT223	SC-73	-	BCP53H					
BCP56-10H			BCP53-10H						
BCP56-16H				BCP53-16H					

1.2 Features and benefits

- High collector current capability I_C and I_{CM}
- Three current gain selections
- High power dissipation capability
- High-temperature applications up to 175 °C
- AEC-Q101 qualified

1.3 Applications

- Linear voltage regulators
- MOSFET drivers
- Low-side switches
- Power management
- Amplifiers

1.4 Quick reference data

Table 2. Quick reference data

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	80	V
I _C	collector current		-	-	1	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	2	Α



Table 2. Quick reference data ...continued

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
h _{FE}	DC current gain	$V_{CE} = 2 \text{ V}; I_{C} = 150 \text{ mA}$	63	-	250	
	BCP56-10H	$V_{CE} = 2 \text{ V}; I_{C} = 150 \text{ mA}$	63	-	160	
	BCP56-16H	$V_{CE} = 2 \text{ V}; I_{C} = 150 \text{ mA}$	100	-	250	

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta = 0.02$

2. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector	4	C
3	E	emitter		В
4	С	collector		E
				sym123

3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
BCP56H	SC-73	plastic surface-mounted package with increased	SOT223		
BCP56-10H		heatsink; 4 leads			
BCP56-16H					

4. Marking

Table 5. Marking codes

Type number	Marking code
ВСР56Н	BCP56H
BCP56-10H	P5610H
BCP56-16H	P5616H

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	N	lin	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-		100	V
V _{CEO}	collector-emitter voltage	open base	-		80	V
V _{EBO}	emitter-base voltage	open collector	-		7	V
Ic	collector current		-		1	Α
I _{CM}	peak collector current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-		2	А
I _B	base current		-		0.2	Α
I _{BM}	peak base current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-		0.3	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u> _		725	mW
			[2] _		1.2	W
			[3]		1.5	W
			[4] _		1.6	W
			[5] _		2.2	W
Tj	junction temperature		-		+175	°C
T _{amb}	ambient temperature			55	+175	°C
T _{stg}	storage temperature		_	65	+175	°C

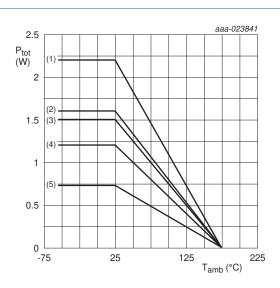
^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm².

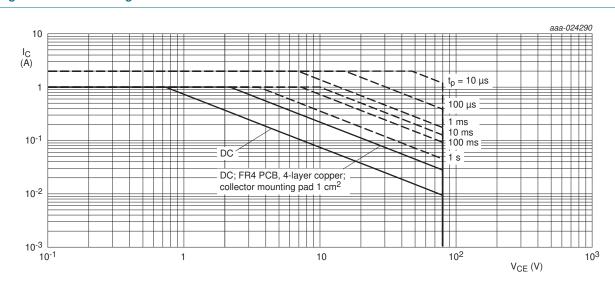
^[4] Device mounted on an FR4 PCB, 4-layer copper; tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper; tin-plated; mounting pad for collector 1 cm².



- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, 4-layer copper, standard footprint
- (3) FR4 PCB, single-sided copper, 6 cm²
- (4) FR4 PCB, single-sided copper, 1 cm²
- (5) FR4 PCB, single-sided copper, standard footprint

Fig 1. Power derating curves



Unless otherwise specified:

 $T_{amb} = 25 \, ^{\circ}C$

Single pulse

FR4 PCB, single-sided copper; standard footprint

Fig 2. Safe operating area; junction to ambient; continuous and peak collector currents as a function of collector-emitter voltage

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	207	K/W
			[2]	-	-	125	K/W
			[3]	-	-	100	K/W
			[4]	-	-	94	K/W
			[5]	-	-	69	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper; tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper; tin-plated; mounting pad for collector 1 cm².

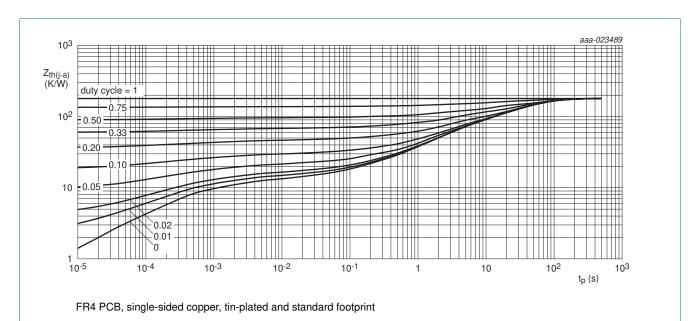
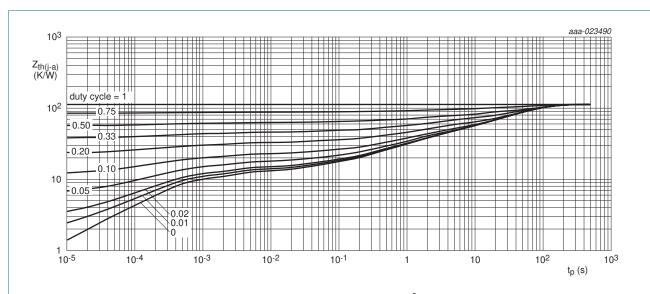
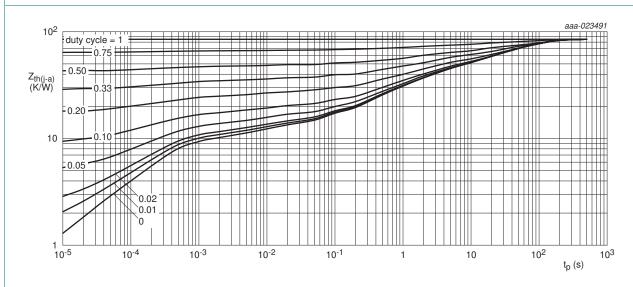


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



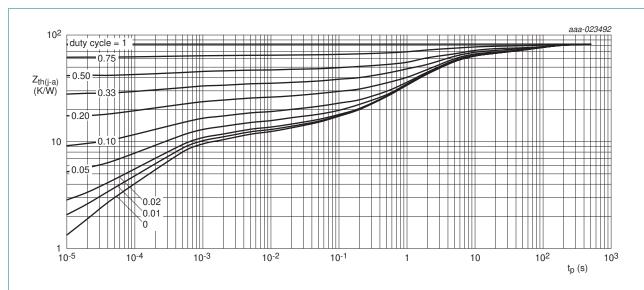
FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm²

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



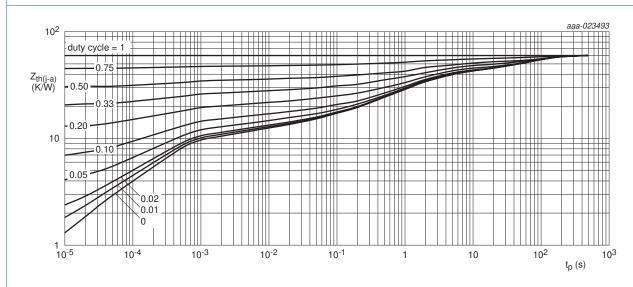
FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm²

Fig 7. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

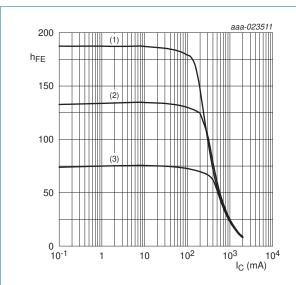
Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO} collector-base cut-off	V _{CB} = 30 V; I _E = 0 A		-	-	100	nA	
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$		-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A		-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 5 mA		63	-	-	
		V _{CE} = 2 V; I _C = 150 mA	[1]	63	-	250	
	V _{CE} = 2 V; I _C = 500 mA	[1]	40	-	-		
	BCP56-10T	V _{CE} = 2 V; I _C = 150 mA	[1]	63	-	160	
	BCP56-16T	V _{CE} = 2 V; I _C = 150 mA	[1]	100	-	250	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	[1]	-	-	500	mV
V _{BE}	base-emitter voltage	V _{CE} = 2 V; I _C = 500 mA	[1]	-	-	1	V
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA};$ f = 100 MHz		100	155	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	4.5	-	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta = 0.02$

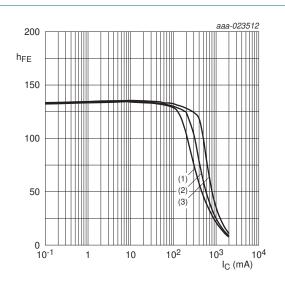
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$$V_{CE} = 2 V$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 8. DC current gain as a function of collector current; typical values



- (1) $V_{CE} = 1 V$
- (2) $V_{CE} = 2 V$
- (3) $V_{CE} = 5 \text{ V}$

Fig 9. DC current gain as a function of collector current; typical values

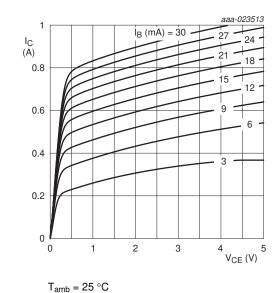
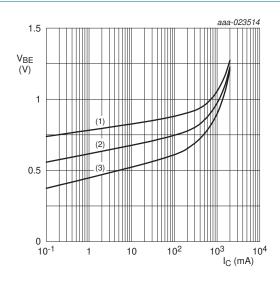


Fig 10. Collector current as a function of collector-emitter voltage; typical values

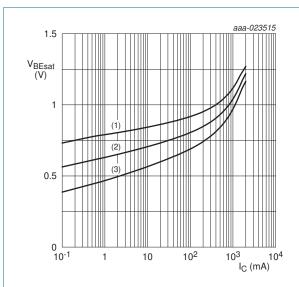


$$V_{CE} = 2 V$$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 11. Base-emitter voltage as a function of collector current; typical values

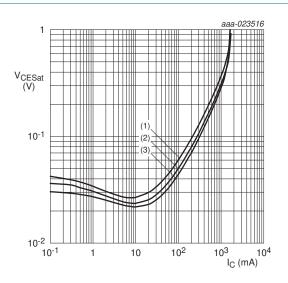
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$$I_{\rm C}/I_{\rm B} = 10$$

- (1) $T_{amb} = -55 \,^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

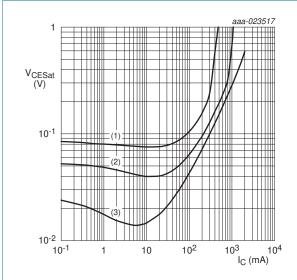
Fig 12. Base-emitter saturation voltage as a function of collector current; typical values



$$I_{C}/I_{B} = 10$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

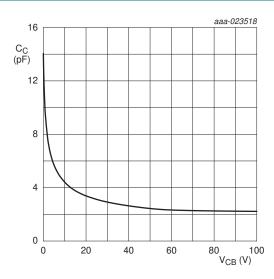
Fig 13. Collector-emitter saturation voltage as a function of collector current; typical values



T_{amb} = 25 °C

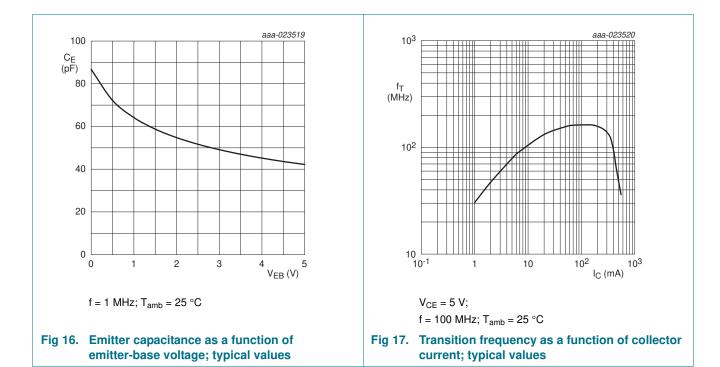
- (1) $I_C/I_B = 50$
- (2) $I_C/I_B = 20$
- (3) $I_C/I_B = 5$

Fig 14. Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz; $T_{amb} = 25 \, ^{\circ}\text{C}$

Fig 15. Collector capacitance as a function of collector-base voltage; typical values

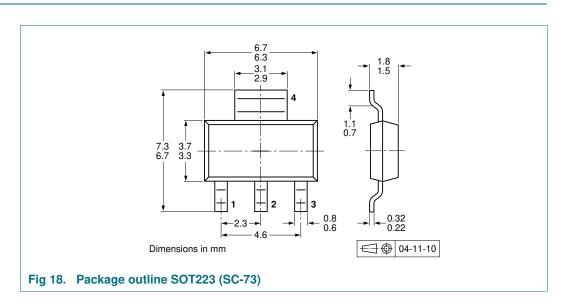


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

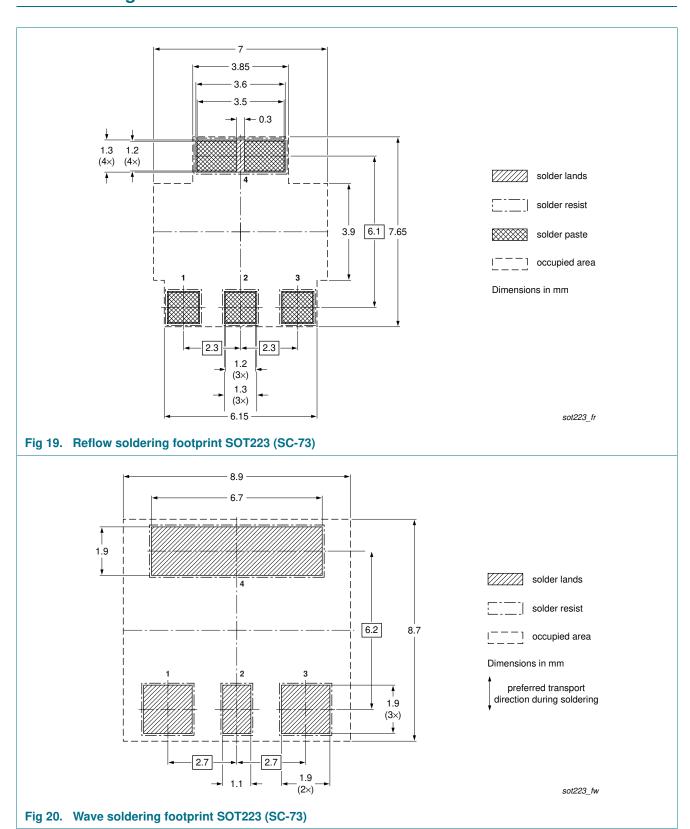


BCP56H_SER

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10. Soldering





11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BCP56H_SER v.1	20161123	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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